

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Rule 1.53(b) Divisional Application of Serial No. 09/102,665:

Hideki MATSUMURA et al.

JC832 U.S. PTO
10/04/1609
01/10/02

Serial No.: Not yet assigned

Group Art Unit: 1763 (Expected)

Filed: January 10, 2002

Examiner: Lund, J. (Expected)

For: **METHOD AND APPARATUS FOR DEPOSITING A THIN FILM,
AND SEMICONDUCTOR DEVICE HAVING A SEMICONDUCTOR-
INSULATOR JUNCTION**

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 CFR 1.97(b)

Commissioner for Patents
Washington, D.C. 20231

January 10, 2002

Sir:

This Information Disclosure Statement is being filed in order to comply with Applicants' duty of disclosure under 37 CFR 1.56. The documents listed on the Form PTO-1449 were made of record in parent Serial No. 09/102,665 filed on June 23, 1998, and grandparent application Serial No. 08/924,304 filed on September 5, 1997.

The Commissioner is authorized to charge our Deposit Account No. 01-2340 for any fee which is deemed by the Patent and Trademark Office to be required to effect consideration of this statement.

Respectfully submitted,

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Enclosure: PTO-1449

**INFORMATION
DISCLOSURE
STATEMENT
PTO-1449**

Atty. Docket No. **971003B** Serial No. Not yet assigned

Applicants: **Hideki MATSUMURA et al.**

Filing Date: **January 10, 2002** Group Art Unit: **1763 (Expected)**

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U.S. PATENT DOCUMENTS

Examiner Initial		Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
	AA	3,652,331	Yamazaki	3/1972	117	201	
	AB	4,237,150	Wiesmann	12/1980	427	74	
	AC	5,160,544	Garg et al.	11/1992	118	724	
	AD	5,366,919	Tanaka et al.	11/1994	437	52	
	AE	5,397,737	Mahan et al.	3/1995	437	101	
	AF	5,795,828	Endo et al.	8/1996	438	678	
	AG	5,840,600	Yamazaki et al.	11/1998	438	151	8/30/1995
	AH	5,149,375	Matsuyama	9/1992	118	719	
	AI	5,693,173	Colombo et al.	12/1997	156	345	12/21/1994
	AJ	5,183,529	Potter et al.	2/1993	156	613	
	AK	5,186,973	Garg et al.	2/1993	427	590	
	AL	5,209,812	Wu et al.	5/1993	156	613	
	AM	5,591,484	Poncelet et al.	1/1997	427	249	11/2/1995
	AN	5,054,421	Ito et al.	10/1991	118	723	
	AO	5,186,973	Garg et al.	10/1991	427	590	
	AP	6,069,094	Matsumura et al.	5/2000	438	788	9/5/1997

FOREIGN PATENT DOCUMENTS

		Document No.	Date	Country	Translation (Yes or No)
	AQ	63-40314	2/1988	Japan	No

INFORMATION DISCLOSURE STATEMENT PTO-1449	Atty. Docket No. 971003B	Serial No. Not yet assigned
Applicants: Hideki MATSUMURA et al.		
	Filing Date: January 10, 2002	Group Art Unit: 1763 (Expected)

OTHER DOCUMENTS

_____	AR	S.Yamazaki et al. SILICON NITRIDE PRERARED BY THE SiH ₄ -NH ₃ REACTION WITH CATALYSIS, Japan Journal of Applied Physics, vol. 9, No. 12, dec. 1970, pp.1467-1477
Examiner	AS	Date Considered